



DMN3016LFDE

## N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BVDSS	Rds(on) max	I <sub>D</sub> max T₄ = +25°C
	12mΩ @ V <sub>GS</sub> = 10V	10A
30V	16mΩ @ V <sub>GS</sub> = 4.5V	8.5A

# **Description and Applications**

This MOSFET has been designed to minimize the on-state resistance  $(R_{DS(ON)})$  and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

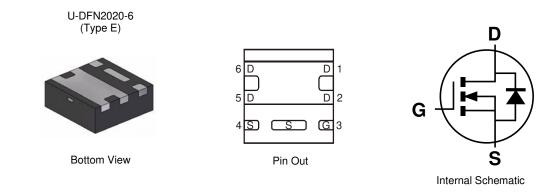
- Battery Management Application
- Power Management Functions
- DC-DC Converters

## **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

## **Mechanical Data**

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)



## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3016LFDE-7	U-DFN2020-6 (Type E)	3,000/Tape & Reel
DMN3016LFDE-13	U-DFN2020-6 (Type E)	10,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



# **Marking Information**

Site 1



$$\label{eq:NR} \begin{split} &\mathsf{NR} = \mathsf{Product} \; \mathsf{Type} \; \mathsf{Marking} \; \mathsf{Code} \\ &\mathsf{YM} = \mathsf{Date} \; \mathsf{Code} \; \mathsf{Marking} \\ &\mathsf{Y} = \mathsf{Year} \; (\mathsf{ex:} \; \mathsf{H} = 2020) \\ &\mathsf{M} = \mathsf{Month} \; (\mathsf{ex:} \; 9 = \mathsf{September}) \end{split}$$

Date Code Kev

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Н	1	J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



NR = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

### Date Code Key

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	2		0	1	2	3	4	5	6	7	8	9
Week	1-26				27	-52		53				
Code	A-Z			a-z				Z				
Internal Code	Sun Mon				Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	V	Х		Y		Z



## Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	30	V		
Gate-Source Voltage	V <sub>GSS</sub>	±20	V		
Continuous Drain Current (Note C) V 10V	Steady State	TA = +25°C TA = +70°C	lo	10 8	А
Continuous Drain Current (Note 6) $V_{GS} = 10V$	t<10s	TA = +25°C TA = +70°C	lD	12 9	А
Maximum Continuous Body Diode Forward Curre	nt (Note 6)		ls	2.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle =	Ідм	90	А		
Avalanche Current (Note 7) L = 0.1mH	I <sub>AS</sub>	22	А		
Avalanche Energy (Note 7) L = 0.1mH			Eas	24	mJ

# Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	TA = +25°C	D-	0.73	W	
Total Power Dissipation (Note 5)	$T_A = +70^{\circ}C$	PD	0.47	vv	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Deve	171	°C/W	
mermai Resistance, Junction to Ambient (Note 5)	t<10s	Reja	121	C/W	
Total Power Dissipation (Note 6)	TA = +25°C	Pp	2.02	W	
Total Power Dissipation (Note 0)	$T_A = +70^{\circ}C$	PD	1.30	vv	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	62		
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	Reja	42	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	Rejc	9.3		
Operating and Storage Temperature Range					

## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

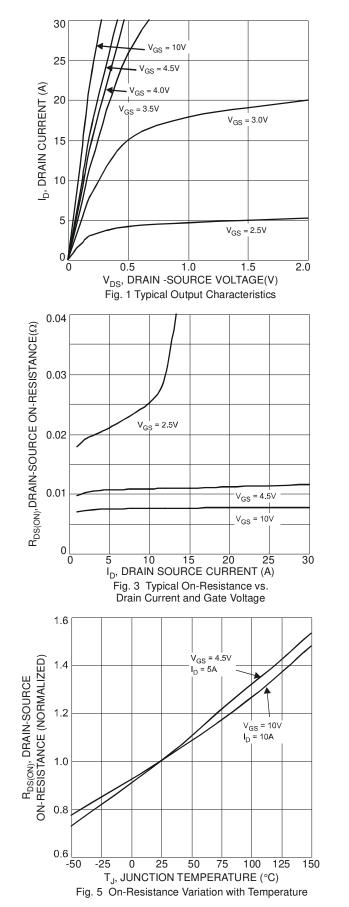
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						·
Drain-Source Breakdown Voltage	BVDSS	30	—	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	IDSS	_	—	1	μA	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	lgss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						·
Gate Threshold Voltage	VGS(TH)	1.4	—	2.0	V	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$
Static Drain-Source On-Resistance		_	8	12	mΩ	VGS = 10V, ID = 11A
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	12	16	11122	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 9A
Forward Transfer Admittance	Y <sub>fs</sub>	_	32	—	S	V <sub>DS</sub> = 5V, I <sub>D</sub> = 12A
Diode Forward Voltage	V <sub>SD</sub>		0.70	1.0	V	$V_{GS} = 0V, I_{S} = 1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	Ciss	_	1415	_		
Output Capacitance	Coss	_	119	_	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	82	_		1 = 1.000HZ
Gate Resistance	Rg	_	2.6	3.2	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1.0MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	11.3	_		
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	25.1		-0	
Gate-Source Charge	Qgs		3.5		nC	$V_{DS} = 15V, I_D = 12A$
Gate-Drain Charge	Qgd	_	3.6	_		
Turn-On Delay Time	tD(ON)		4.8			
Turn-On Rise Time	tR	_	16.5	—		$V_{DD} = 15V, V_{GS} = 10V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		26.1	—	ns	$R_L = 1.25\Omega, R_G = 3\Omega$
Turn-Off Fall Time	tF	_	5.6	_		
Reverse Recovery Time	trr	_	12.3	_	ns	
Reverse Recovery Charge	Q <sub>RB</sub>		10.4		nC	IF = 12A, di/dt = 500A/µs

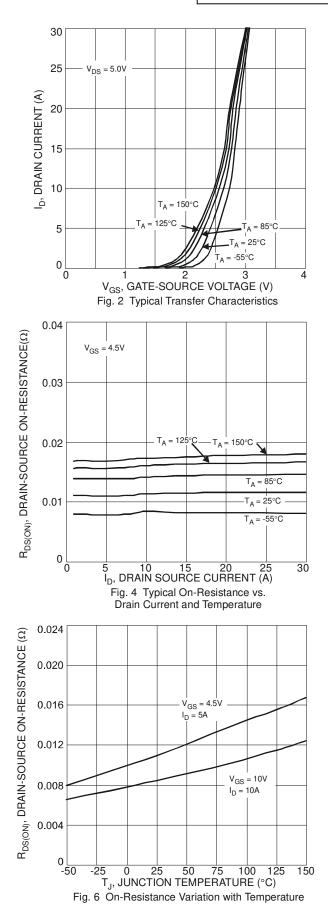
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. I<sub>AS</sub> and E<sub>AS</sub> ratings are based on low frequency and duty cycles to keep  $T_J = +25^{\circ}C$ . 8. Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.

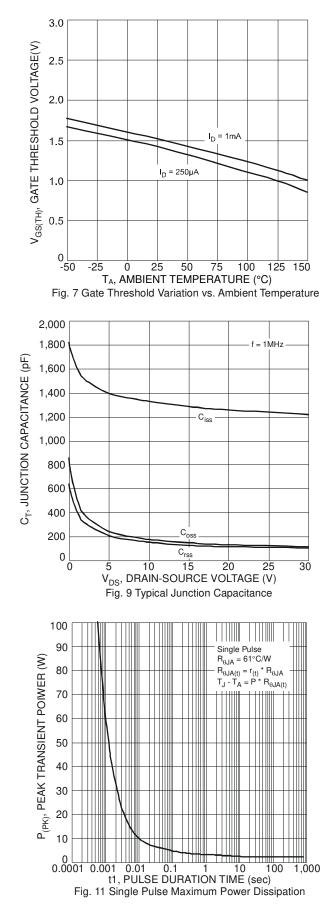


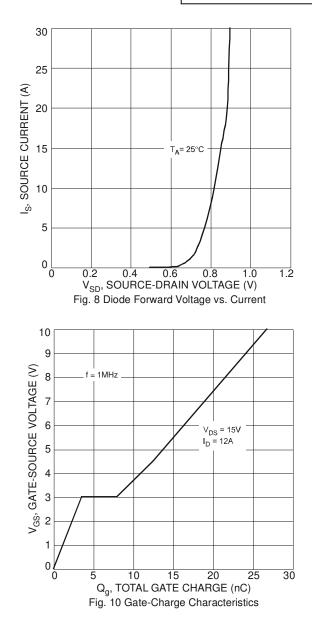
# DMN3016LFDE



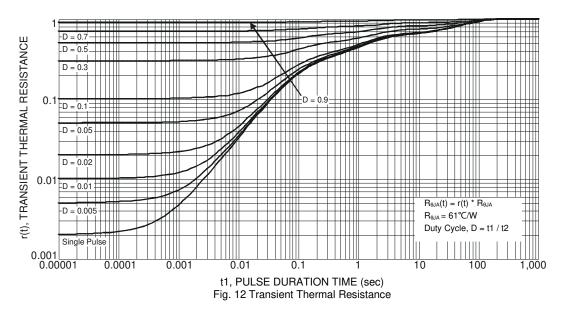








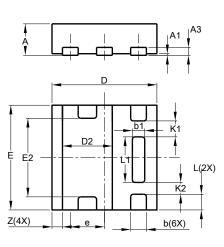






## **Package Outline Dimension**

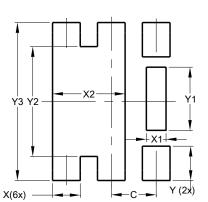
Please see http://www.diodes.com/package-outlines.html for the latest version.



	U-DF	N2020-	·6					
	Ту	/pe E	Тур					
Dim	Min							
Α	0.57	0.63	0.60					
A1	0	0.05	0.03					
A3	-	-	0.15					
b	0.25	0.35	0.30					
b1	0.185	0.285	0.235					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
E	1.95	2.05	2.00					
E2	1.40	1.60	1.50					
е	-	-	0.65					
L	0.25	0.35	0.30					
L1	0.82	0.92	0.87					
K1	-	_	0.305					
K2	-	_	0.225					
Z	-	_	0.20					
All	Dimen	isions i	in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



## U-DFN2020-6 (Type E)

Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

U-DFN2020-6 (Type E)



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